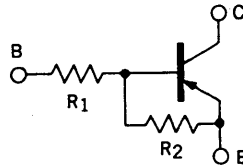


NEC

PNP SILICON TRANSISTOR BN1L4L

DESCRIPTION The BN1L4L is designed for use in medium speed switching circuit.

FEATURE • Bias resistors built-in type PNP transistor equivalent circuit.



$R_1 = 47 \text{ k}\Omega$
 $R_2 = 22 \text{ k}\Omega$

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

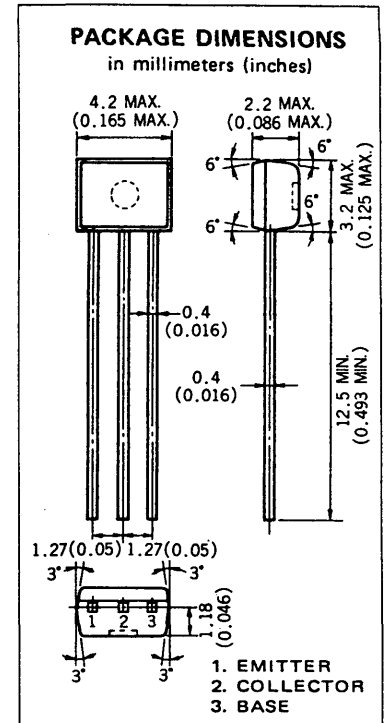
Storage Temperature -55 to $+150$ °C
Junction Temperature 150 °C Maximum

Maximum Power Dissipation ($T_a = 25$ °C)

Total Power Dissipation 250 mW

Maximum Voltages and Currents ($T_a = 25$ °C)

V_{CBO} Collector to Base Voltage -60 V
 V_{CEO} Collector to Emitter Voltage -50 V
 V_{EBO} Emitter to Base Voltage -15 V
 $I_{C(DC)}$ Collector Current (DC) -100 mA
 $I_{C(pulse)}$ Collector Current (pulse) -200 mA



ELECTRICAL CHARACTERISTICS ($T_a = 25$ °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
R_1	Input Resistance	32.9	47.0	61.1	$\text{k}\Omega$	
R_2	Input Resistance	15.4	22.0	28.6	$\text{k}\Omega$	
V_{IL}	Low Level Input Voltage		-1.83	-0.9	V	$V_{CE} = -5.0 \text{ V}, I_C = -100 \mu\text{A}$
V_{IH}	Hi Level Input Voltage	-6.0	-3.0		V	$V_{CE} = -0.2 \text{ V}, I_C = -5.0 \text{ mA}$
t_{on}	Turn On Time		0.5	1.0	μs	$V_{CC} = -5.0 \text{ V}, R_L = 1.0 \text{ k}\Omega,$ $V_{in} = -5.0 \text{ V},$ $PW = 2 \mu\text{s}, \text{Duty Cycle} \leq 2\%$
t_{stg}	Storage Time		0.6	3.0	μs	
t_{off}	Turn Off Time		0.9	5.0	μs	
h_{FE1}	DC Current Gain	60	95	195	—	$V_{CE} = -5.0 \text{ V}, I_C = -5.0 \text{ mA}$
h_{FE2}	DC Current Gain	90	185		—	$V_{CE} = -5.0 \text{ V}, I_C = -50 \text{ mA}$
$V_{CE(sat)}$	Collector Saturation Voltage		-0.04	-0.2	V	$I_C = -5.0 \text{ mA}, I_B = -0.25 \text{ mA}$
I_{CBO}	Collector Cutoff Current			-0.1	μA	$V_{CB} = -50 \text{ V}, I_E = 0$

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

